

RPC DRAM Powerful & Miniaturized

What is **RPC DRAM**[®] and why does it matter?

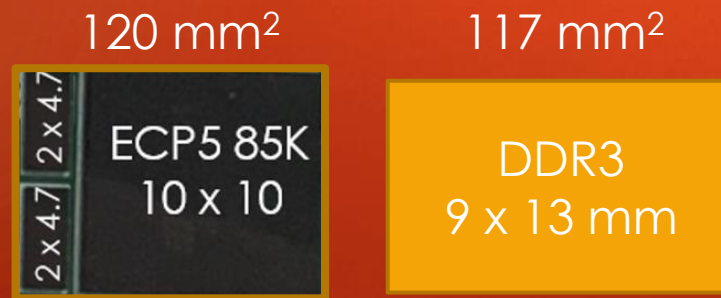
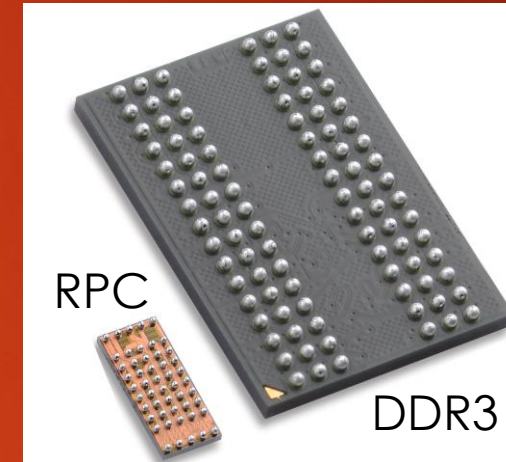
▶ RPC DRAM

- ▶ 256Mbits
- ▶ High Bandwidth (DDR3 speed)
- ▶ Half the pins of DDR3
- ▶ 1/10 the PCB Footprint of DDR3

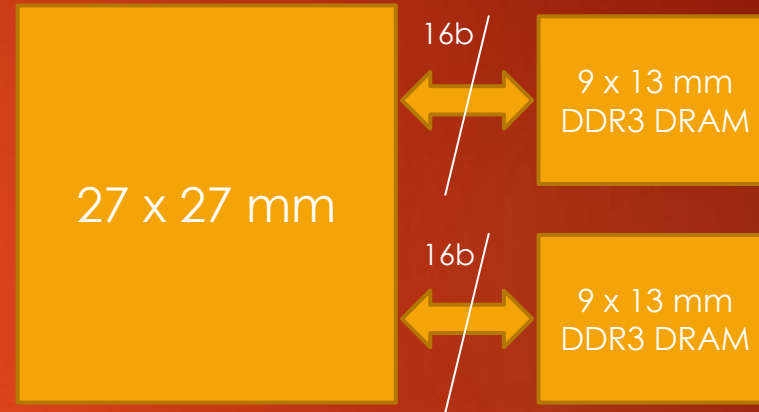
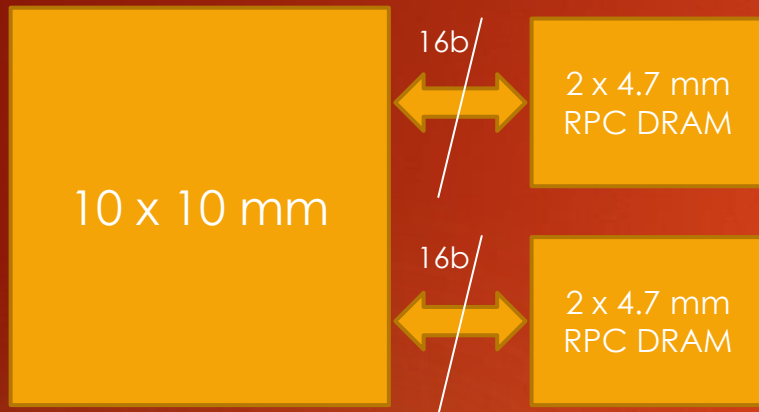
▶ Combined with ECP5 family in 285 csfBGA:

- ▶ Area of two RPC DRAMs + 1 FPGA ~ same PCB space as 1 pc of x16 DDR3

RPC[®] vs DDR3
Same bandwidth
Half the IO pins
10% of PCB area



Form factor Comparison

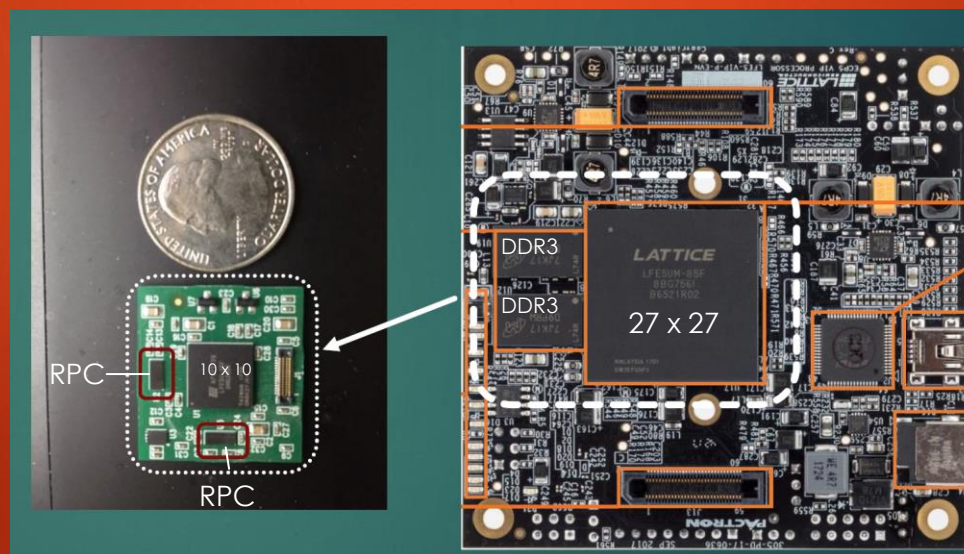


Minimum RPC cap'y: 256 Mbit/chip

Minimum DDR3 cap'y: 1 Gbit/chip

512 Mbits of RPC

1 ea 10 x 10 mm ECP5 85K
(285 csfBGA)
2 pcs 2 x 4.7 mm RPC DRAM



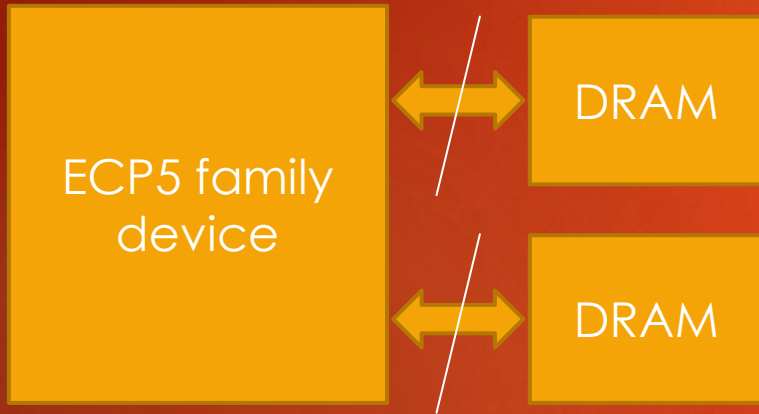
2 Gbits of DDR3
(4K application requires 272 Mbits)

1 ea 27 x 27mm ECP5 85K
2 pcs 9 x 13 mm DDR3 DRAM

ECP5 4K Video Implementation

16 bits / channel
Up to DDR400 / channel

For Write/Read 4K at full bandwidth:
(need 2x incoming video rate at minimum)



Required memory bandwidth (write + read at video source rate):

$2 \times 1024 \text{ Mbytes / sec} = 2048 \text{ Mbytes / sec}$

Memory DDR Clock Speed for 1 Channel:

1 channel @ 256 MHz provides 1024 Mbytes/sec: half of what's needed: must use 2 channels @ 256 MHz

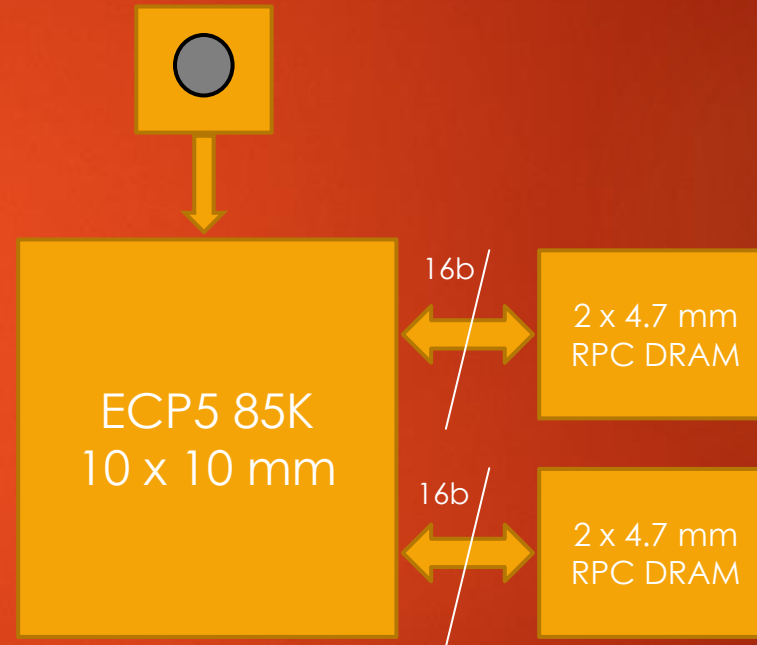
	Minimum Single IC Memory Capacity (Mbits)	# Mbits needed for one 4K frame	# IOs for x16 channel	# IOs for x32 lockstep channel	Minimum Memory Mbits (x16 channel)	Excess (wasted) Mbits (one channel)	Minimum Memory Mbits (x32 channel)	Excess (wasted) Mbits (two channel)
RPC	256	136.8576	24	48	256	119.1424	512	238.2848
DDR3	1024	136.8576	51	73	1024	887.1424	2048	1774.2848

Miniaturized Module

ECP5 + 2 RPC DRAM + AF Camera

5

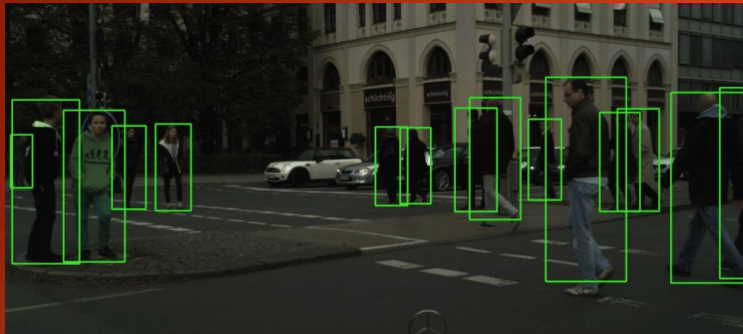
Etron
9/24/2020



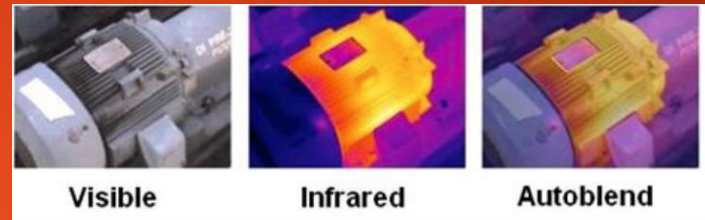
Example AI / Vision Applications ECP5 + Two RPC DRAMs

6

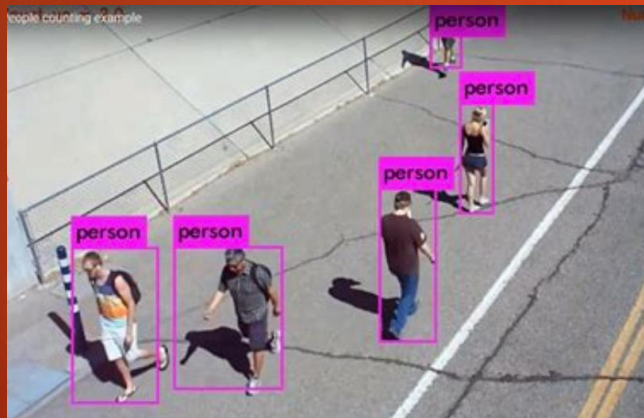
Etron
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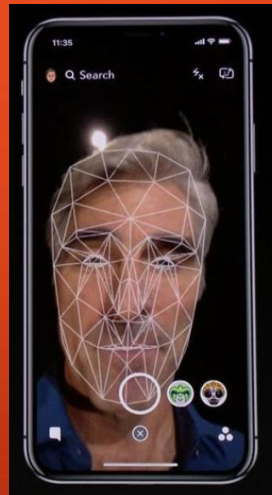
Social Distance Monitoring



Visible / Thermal image fusion



People Counting / Traffic analysis

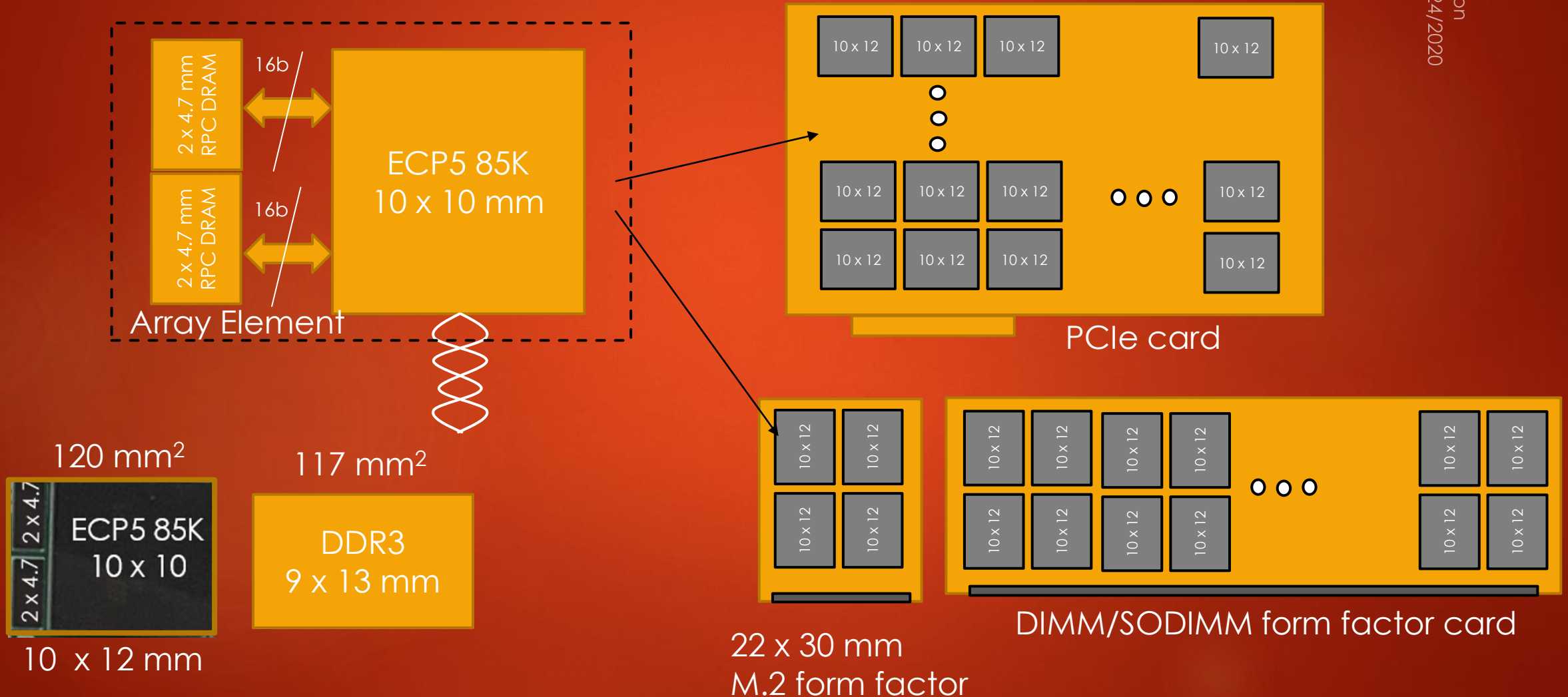


Face ID



Lens Distortion Correction / Rectification

AI/Search/Signal Processing Array Element ECP5 + 2 RPC DRAM w / SERDES



Design Support We Offer

- ▶ RPC DRAM Data Sheet
- ▶ RPC DRAM Memory Controller
 - ▶ Compatible with Lattice Diamond Tools
 - ▶ Compatible with SensAI Neural Network Compiler
- ▶ Verilog Model of RPC DRAM
- ▶ Reference Design Documentation / examples
- ▶ Design support services (provided by Intermotion Technology Inc.)
- ▶ Embedded Vision Development Kit Board (after 3Q '20, contact sales)

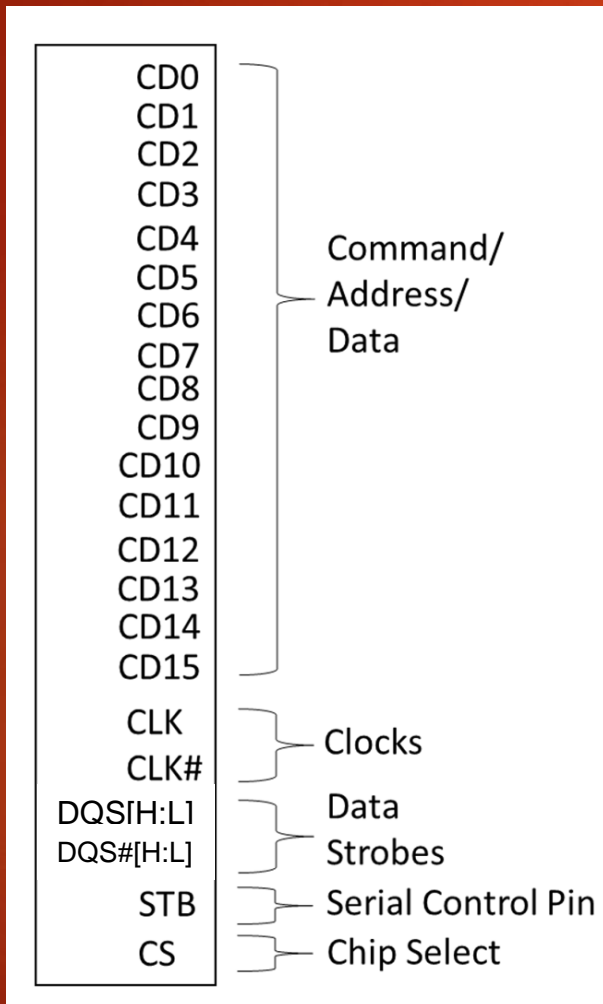
www.etrnamerica.com

www.latticesemi.com

www.intermiontech.com

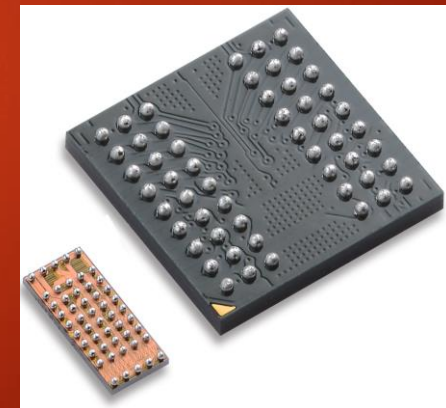
RPC DRAM Backgrounder

RPC DRAM®



- ▶ 256 Mbits
- ▶ 4 banks of 64 Mbits
- ▶ X16 DDR type external interface
- ▶ Memory bus clock up to 1200 MHz (DDR2400)
- ▶ 22/24 IO pin interface
- ▶ Discrete Packaging
 - ▶ 54 BGA (8 x 8 mm)
 - ▶ 50 WLCSP (2 x 4.7 mm)
- ▶ Bare Die (2 x 4.7 mm KGD)
- ▶ Speeds up to DDR 2400
- ▶ 1.35 & 1.5V versions

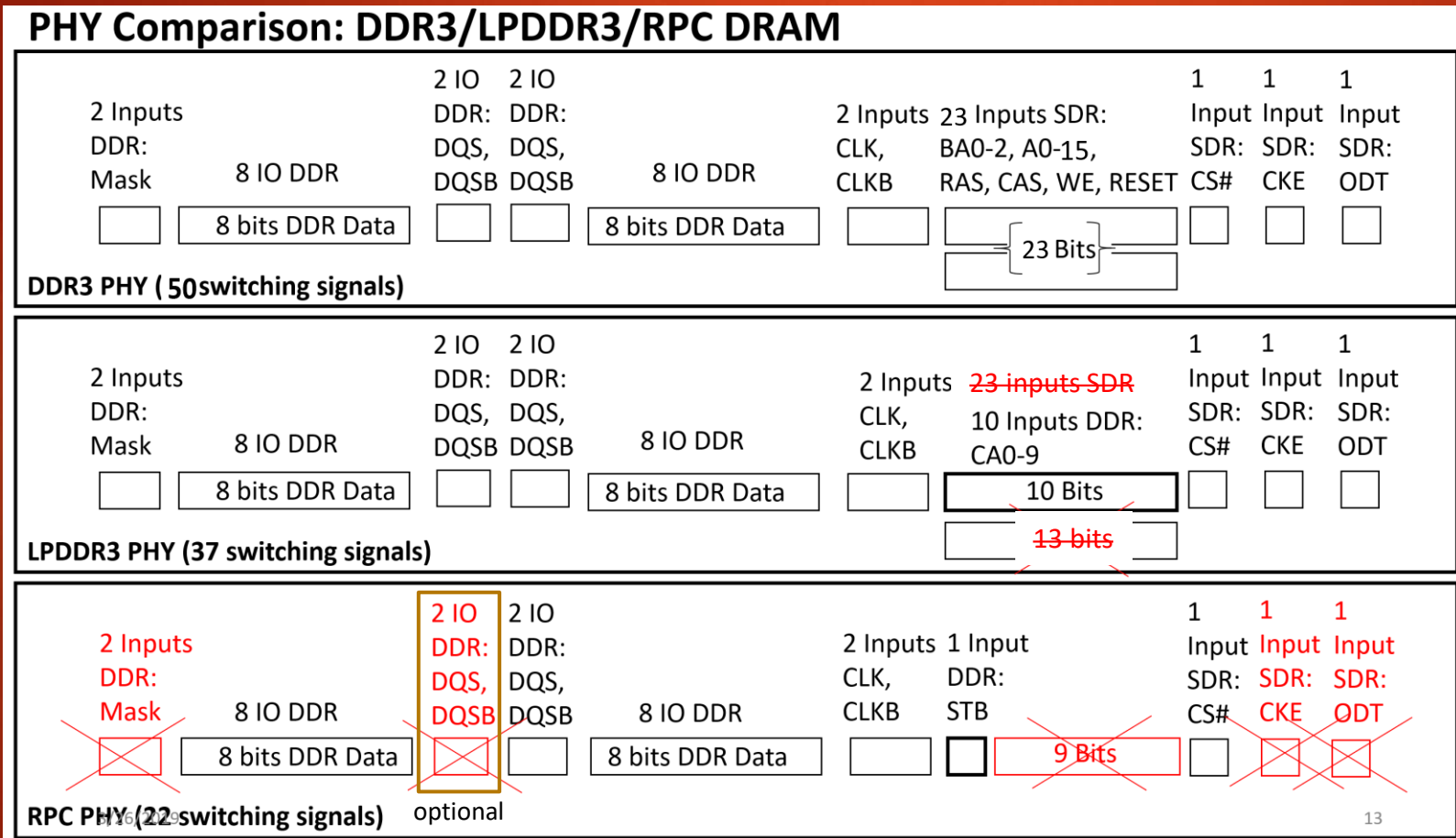
54 BGA (8 x 8 mm)



50 WLCSP (2 x 4.7 mm)

Interface Signal Comparison

DDR3, LPDDR3, RPC



DDR3/LPDDR3 vs RPC Architecturally Similar

12

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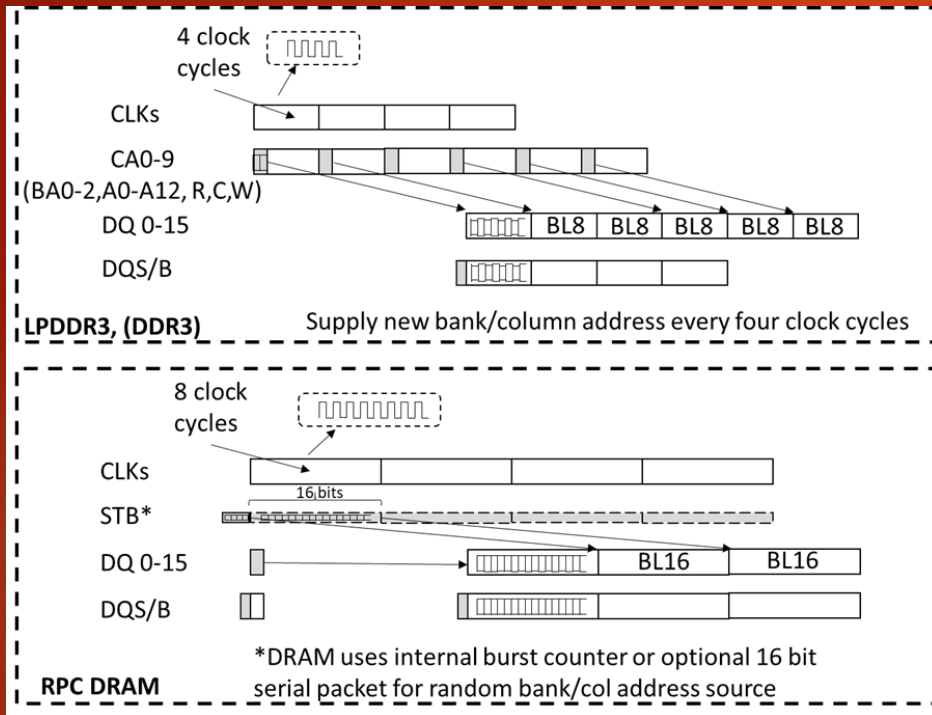


Table 65: Command Truth Table

Notes 1-13 apply to entire table

Command	Command Pins				CA Pins															CK Edge
	CK(n-1)	CK(n)	CS _n	CA0	CA1	CA2	CA3	CA4	CA5	CA6	CA7	CA8	CA9	MA0	MA1	MA2	MA3	MA4	MA5	
MRW	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
MRR	H	H	X	MA6	MA7	OP0	OP1	OP2	OP3	OP4	OP5	OP6	OP7							
REFRESH (per bank)	H	H	X	MA6	MA7					X										
REFRESH (all banks)	H	H	X							X										
Enter self refresh	H	L	X							X										
ACTIVATE (bank)	H	H	X	R0	R1	R2	R3	R4	R5	R6	R7	R8	R9	R10	R11	R12	BA0	BA1	BA2	
WRITE (bank)	H	H	X	AP	C3	C4	C5	C6	C7	C8	C9	C10	C11				BA0	BA1	BA2	
READ (bank)	H	H	X	AP	C3	C4	C5	C6	C7	C8	C9	C10	C11				BA0	BA1	BA2	
PRECHARGE (per bank, all banks)	H	H	X							X							BA0	BA1	BA2	
ENTER DPD	H	L	X							X										
NOP	H	H	X							X										
MAINTAIN PD, SREF, DPD (NOP)	L	L	X							X										
NOP	H	H	X							X										

LPDDR3 receives Encoded Address/Commands via double edged command/address bus sampling

LPDDR3 Command Truth Table

Table 6-1. Parallel Packet Command Truth Table

Command	CLK		CS#	DB Pins																	
	CK _{n-1}	CK _n		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0		
MRS	0	0	0	ODT	CS#	FX	STB		ZQ#									CL	0	1	0
ACT	0	0	0	X			RA11	RA10	RA9	RA8	RA7	RA6	RA5	RA4	RA3	RA2	RA1	RA0	0	0	1
RD	0	0	0	CA5	CA5	CA4												BA1	BA0	0	0
WR	0	0	0	CA9	CA8	CA7												BA1	BA0	0	0
WL-2 (1st DM)	0	0	0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0
WL-1 (last DM)	0	0	0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0	DM1	DM0
PRE	0	0	0				X														
BEE	0	0	0				X			BK3	BK2	BK1	BK0								
PD Entry	0	0	0							X									REF	OP1	OP0
PD Exit	0	0	0							X											
DPD Entry	0	0	0							X											
DPD Exit	0	0	0							X											
ZQ Calibration	0	0	0	ZQC	OP1	ZQC	OP0				X										
RESET	0	0	0							X											
UTR	0	0	0							X									UTR	OP1	OP0
	0	0	0								X								UTR	EN	

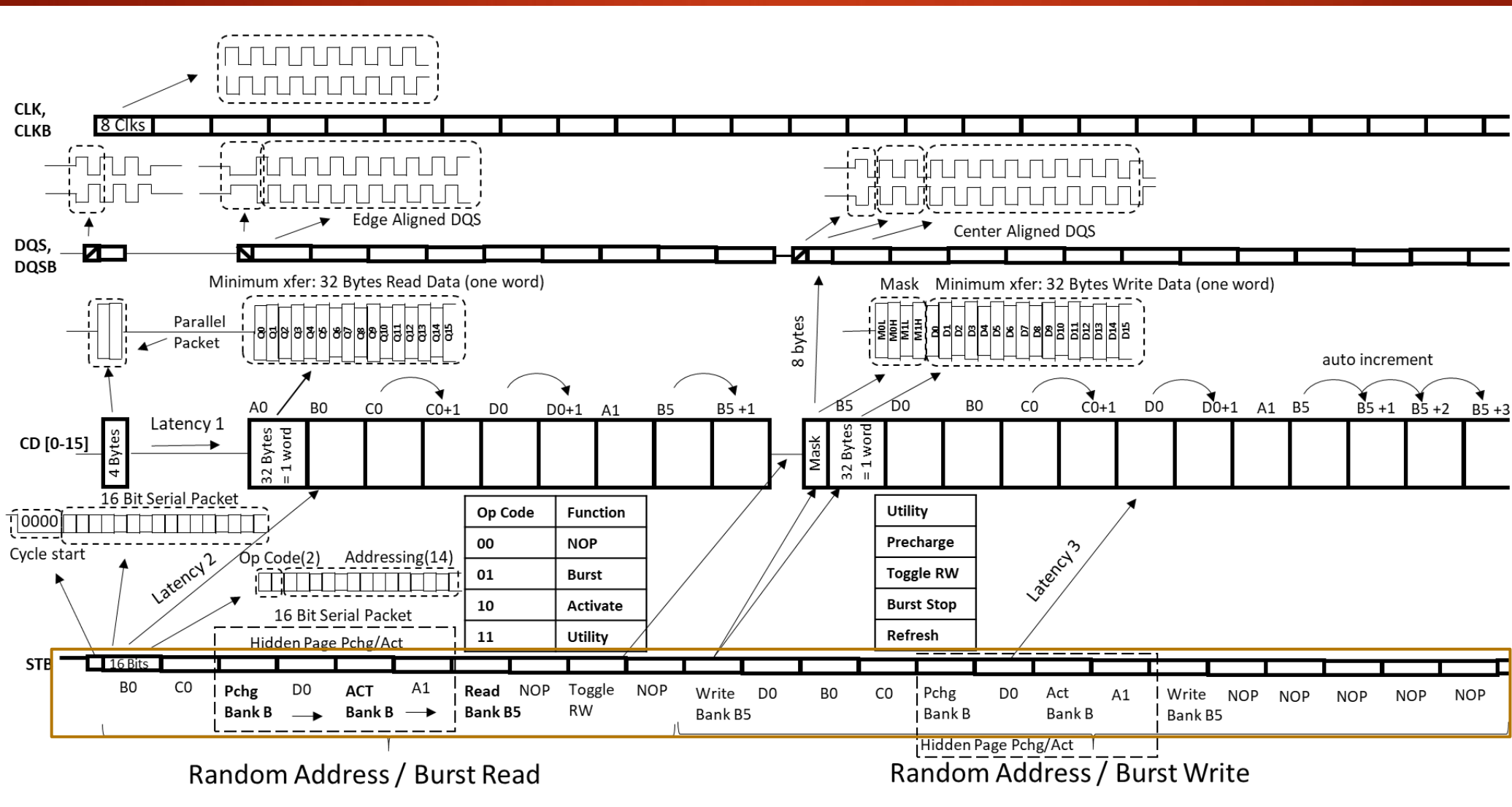
RPC DRAM receives Encoded Address/Commands via double edged command/address bus sampling

DDR3, LPDDR3 & RPC DRAM Main Architectural Differences

Device	X16 DDR3 (256M)	X16 LPDDR3 (256M)	X16 RPC DRAM (256M)
Banks	4	4	4
Arch. Prefetch	128 bits	128 bits	256 bits
Burst Cycle Addressing	New address every 4 clocks	New address every 4 clocks	Internal burst counter -or- Optional new col/bank address every 8 clocks
PHY Signals	51	37	22/24
CA Ports	1: SDR, Separate from Data	1: DDR, Separate from Data	2: DDR, parallel packet port is multiplexed with Data & Serial packet port (STB pin) is separate from Data

RPC DRAM Command Truth Table

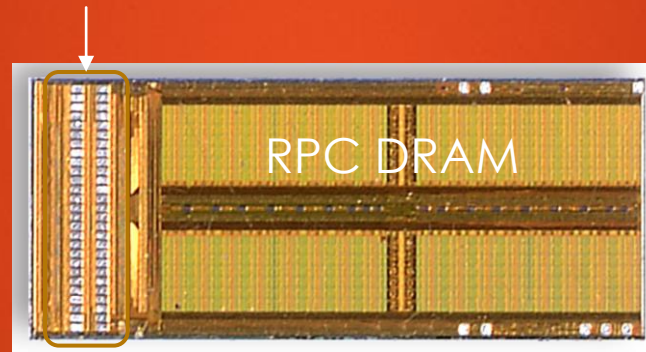
RPC Serial Control Protocol



Alternative Packaging

Bare Die for MCPs

Bonding Pads
(one end only)

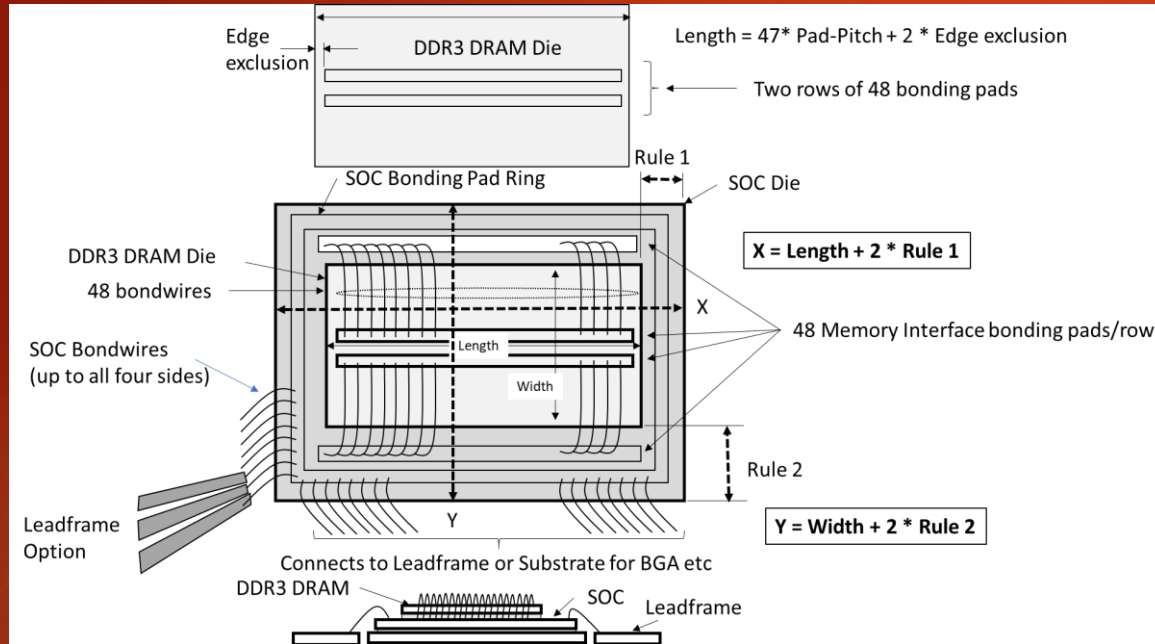


4.63 x 1.96 mm

Stacked Die Assembly for MCP w/DRAM

16

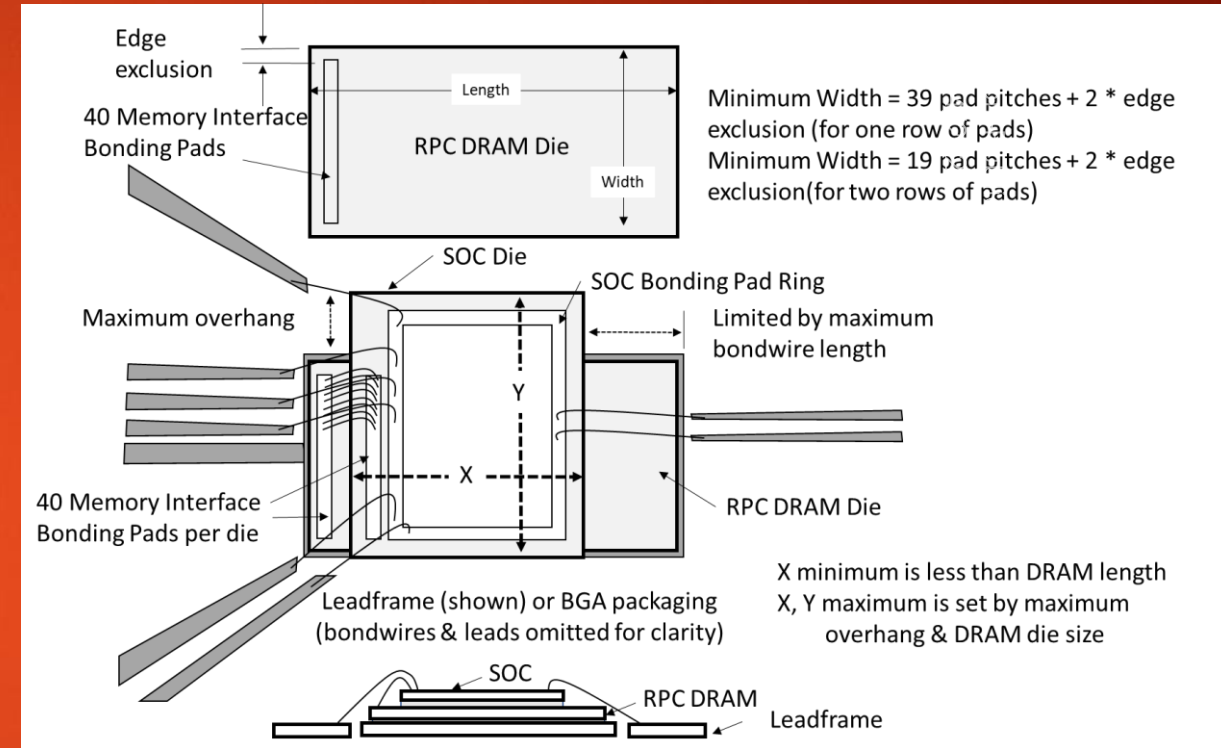
DDR3



DRAM LIMITED

MCP with Stacked die using DDR3 DRAM on top: DRAM establishes minimum SOC die size

RPC DRAM



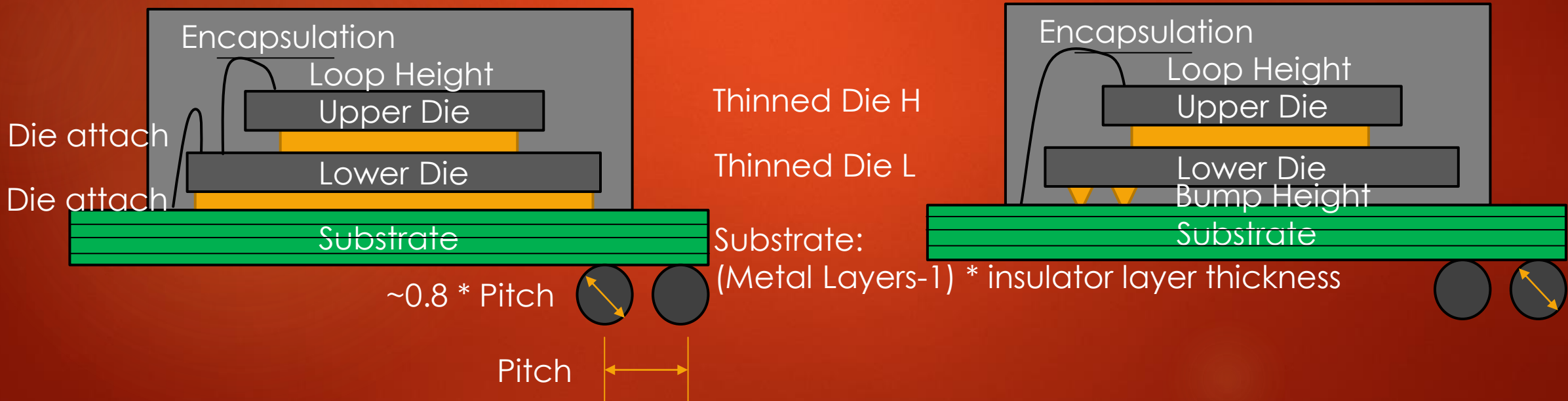
SOC is core or pad LIMITED

MCP with Stacked die using SOC on top of stairstep stack with RPC DRAM allows for much smaller SOC die mechanical size

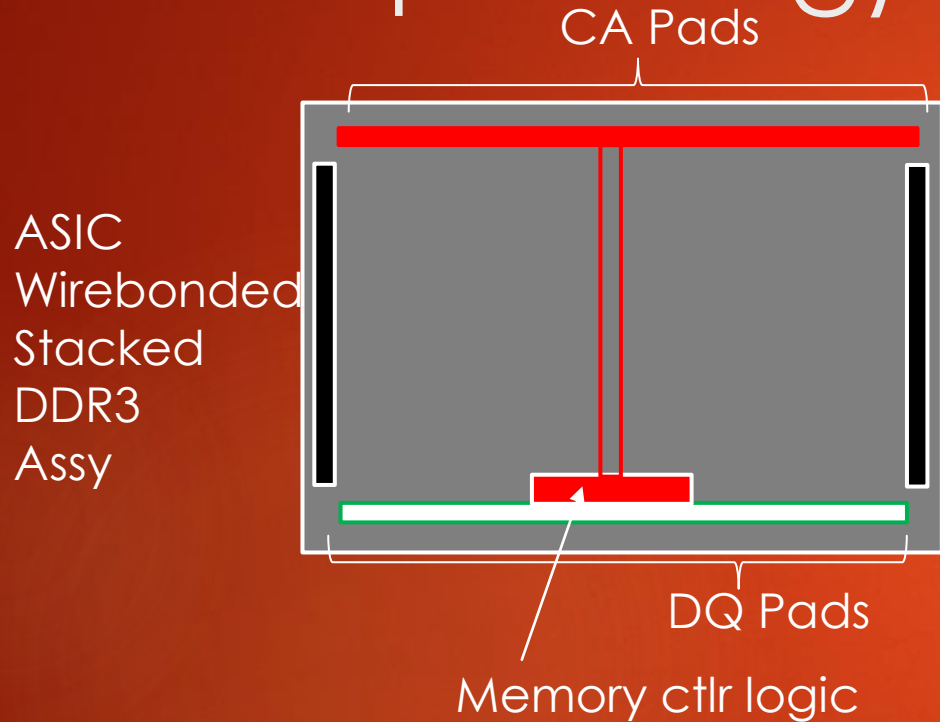
Assembly Rules Impact on SOC Die Size

Wirebonded MCP Cross Section Design Rules

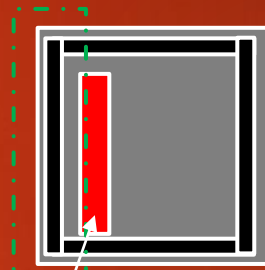
All Dimensions are in Microns											
	Pitch	Ball Size (0.8 * ball pitch)	Substrate Metal Layer Count	Thickness: substrate insulator layer	Lower Die attach Thickness or FC Bump Height	Lower Die Thickness	Upper Die Attach Thickness	Upper Die Thickness	Wire Loop Height	Encapsulation	Package Thickness (board to top)
Wirebond	400	320	4	50	35	100	35	100	150	50	940
FC	400	320	4	50	75	100	35	100	150	50	980



RPC Value Proposition (ASIC Floorplanning)



ASIC
Wirebonded
Stacked
RPC
Assy

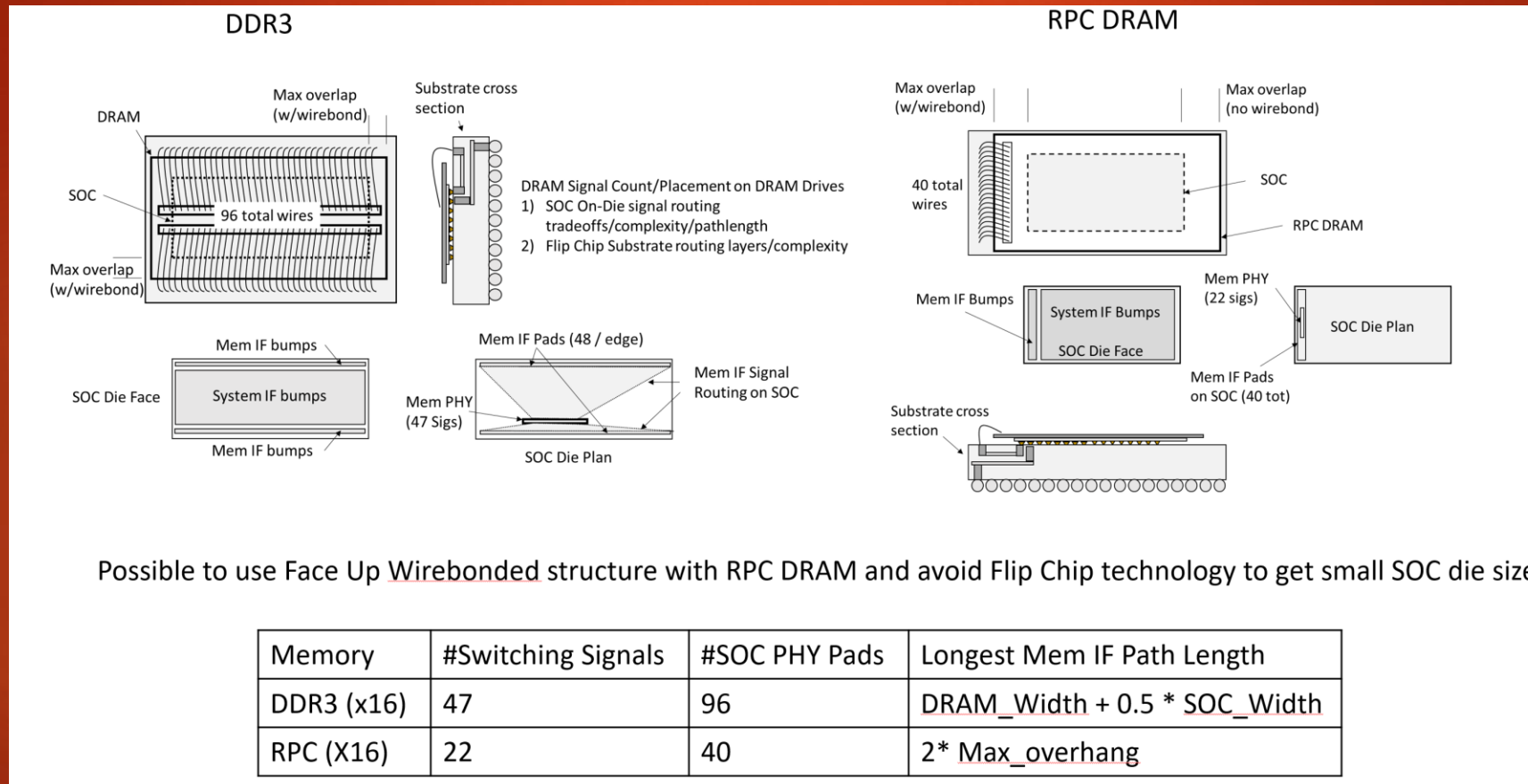


Memory ctrl logic

Mem I/F pads adjacent to Mem Ctlr Logic
(everything remains together on the die)

Must route many signals across chip or route through substrate
(address/control and data must bond to opposite sides of the ASIC, but all come from memory controller)

Flip Chip ASIC/SOC with Stacked Die Memory

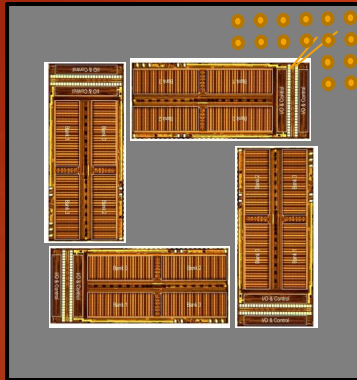


168 ball POP/standalone Memory x64, 1 Gbit, 19.2 GBytes/sec

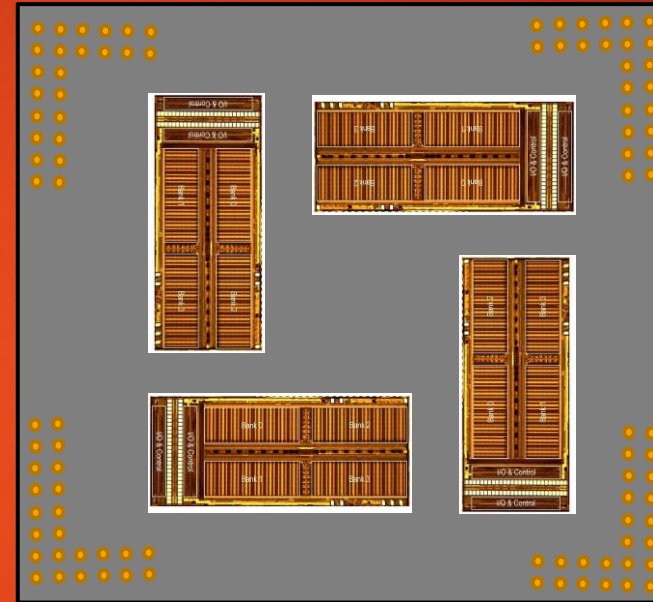
20

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23 ball x 23 ball array, 500 micron pitch



12 x 12 mm



0.325 ball,
0.500 pitch

